

Detlev A GrÃ¼tzmacher

List of Publications by Year in descending order

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315
papers

8,852
citations

50170

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64668

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g-index

322
all docs

322
docs citations

322
times ranked

7265
citing authors

#	ARTICLE	IF	CITATIONS
1	Lasing in direct-bandgap GeSn alloy grown on Si. Nature Photonics, 2015, 9, 88-92.	15.6	1,016
2	Intersubband Electroluminescence from Silicon-Based Quantum Cascade Structures. Science, 2000, 290, 2277-2280.	6.0	272
3	Optically Pumped GeSn Microdisk Lasers on Si. ACS Photonics, 2016, 3, 1279-1285.	3.2	195
4	Three-Dimensional Si/Ge Quantum Dot Crystals. Nano Letters, 2007, 7, 3150-3156.	4.5	175
5	Anomalous Coiling of SiGe/Si and SiGe/Si/Cr Helical Nanobelts. Nano Letters, 2006, 6, 1311-1317.	4.5	163
6	Fabrication and Characterization of Three-Dimensional InGaAs/GaAs Nanosprings. Nano Letters, 2006, 6, 725-729.	4.5	155
7	Interface and Wetting Layer Effect on the Catalyst-Free Nucleation and Growth of GaN Nanowires. Small, 2008, 4, 751-754.	5.2	145
8	Band engineering and growth of tensile strained Ge/(Si)GeSn heterostructures for tunnel field effect transistors. Applied Physics Letters, 2013, 102, .	1.5	131
9	Controllable fabrication of SiGe/Si and SiGe/Si/Cr helical nanobelts. Nanotechnology, 2005, 16, 655-663.	1.3	128
10	A new technique for fabricating three-dimensional micro- and nanostructures of various shapes. Nanotechnology, 2001, 12, 399-402.	1.3	126
11	Room-Temperature High-Frequency Transport of Dirac Fermions in Epitaxially Grown SbBi Nanowires. Physical Review Letters, 2014, 113, 096601.	2.9	101
12	Impact of sidewall recombination on the quantum efficiency of dry etched InGaAs/InP semiconductor wires. Applied Physics Letters, 1989, 54, 1552-1554.	1.5	95
13	Raman scattering of phonon-plasmon coupled modes in self-assembled GaN nanowires. Journal of Applied Physics, 2009, 105, .	1.1	91
14	Impact of nanometer-scale roughness on contact-angle hysteresis and globulin adsorption. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 1715.	1.6	90
15	MBE growth optimization of topological insulator Bi ₂ Te ₃ films. Journal of Crystal Growth, 2011, 324, 115-118.	0.7	90
16	Hall effect measurements on InAs nanowires. Applied Physics Letters, 2012, 101, 152106.	1.5	88
17	Electroluminescence from strain-compensated Si _{0.2} Ge _{0.8} /Si quantum-cascade structures based on a bound-to-continuum transition. Applied Physics Letters, 2002, 81, 4700-4702.	1.5	87
18	Band-gap renormalization and band-filling effects in a homogeneous electron-hole plasma in In _{0.53} Ga _{0.47} As/InP single quantum wells. Physical Review B, 1989, 40, 8087-8090.	1.1	86

#	ARTICLE	IF	CITATIONS
19	Realization of a vertical topological p-n junction in epitaxial Sb ₂ Te ₃ /Bi ₂ Te ₃ heterostructures. Nature Communications, 2015, 6, 8816.	5.8	85
20	Interface-roughness-induced broadening of intersubband electroluminescence in p-SiGe and n-GaInAs/AlInAs quantum-cascade structures. Applied Physics Letters, 2005, 86, 062113.	1.5	83
21	Optical Transitions in Direct-Bandgap Ge _{1-x} Sn _x Alloys. ACS Photonics, 2015, 2, 1539-1545.	3.2	83
22	Spin-orbit coupling and phase coherence in InAs nanowires. Physical Review B, 2010, 82, .	1.1	79
23	Signatures of interaction-induced helical gaps in nanowire quantum point contacts. Nature Physics, 2017, 13, 563-567.	6.5	77
24	Dimer Pairing on the C-Alloyed Si(001) Surface. Physical Review Letters, 1999, 82, 972-975.	2.9	73
25	Ga-assisted MBE growth of GaAs nanowires using thin HSQ layer. Journal of Crystal Growth, 2012, 353, 39-46.	0.7	71
26	Molecular Beam Epitaxy Growth of GaAs/InAs Core-Shell Nanowires and Fabrication of InAs Nanotubes. Nano Letters, 2012, 12, 5559-5564.	4.5	71
27	Selective area growth and stencil lithography for in situ fabricated quantum devices. Nature Nanotechnology, 2019, 14, 825-831.	15.6	70
28	Electronic Phase Coherence in InAs Nanowires. Nano Letters, 2011, 11, 3550-3556.	4.5	68
29	Reduced Pressure CVD Growth of Ge and Ge _{1-x} Sn _x Alloys. ECS Journal of Solid State Science and Technology, 2013, 2, N99-N102.	0.9	67
30	Photon drag effect in Bi_2Te_3 topological insulators. Physical Review B, 2016, 93, .	1.1	67
31	Bi ₂ Te ₃ is a dual topological insulator. Nature Communications, 2017, 8, 14976.	5.8	66
32	Freestanding SiGe/Si/Cr and SiGe/Si/SixNy/Cr microtubes. Applied Physics Letters, 2004, 84, 3391-3393.	1.5	65
33	X-ray Nanodiffraction on a Single SiGe Quantum Dot inside a Functioning Field-Effect Transistor. Nano Letters, 2011, 11, 2875-2880.	4.5	65
34	Tensely strained GeSn alloys as optical gain media. Applied Physics Letters, 2013, 103, .	1.5	63
35	Mode of Growth of Ultrathin Topological Insulator Bi ₂ Te ₃ Films on Si (111) Substrates. Crystal Growth and Design, 2012, 12, 6098-6103.	1.4	62
36	Three-dimensional nanosprings for electromechanical sensors. Sensors and Actuators A: Physical, 2006, 130-131, 54-61.	2.0	61

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37	Effect of Si-doping on InAs nanowire transport and morphology. Journal of Applied Physics, 2011, 110, .	1.1	61
38	Advanced GeSn/SiGeSn Group IV Heterostructure Lasers. Advanced Science, 2018, 5, 1700955.	5.6	61
39	Suppressing Twin Domains in Molecular Beam Epitaxy Grown Bi ₂ Te ₃ Topological Insulator Thin Films. Crystal Growth and Design, 2015, 15, 390-394.	1.4	59
40	Ge segregation in SiGe/Si heterostructures and its dependence on deposition technique and growth atmosphere. Applied Physics Letters, 1993, 63, 2531-2533.	1.5	58
41	Robust surface electronic properties of topological insulators: Bi ₂ Te ₃ films grown by molecular beam epitaxy. Applied Physics Letters, 2011, 98, 222503.	1.5	56
42	Self-catalyzed VLS grown InAs nanowires with twinning superlattices. Nanotechnology, 2013, 24, 335601.	1.3	56
43	Mode of growth in LP-MOVPE deposition of GaInAs/InP quantum wells. Journal of Electronic Materials, 1990, 19, 471-479.	1.0	55
44	Field effect transistor based on single crystalline InSb nanowire. Journal of Materials Chemistry, 2011, 21, 2459.	6.7	54
45	Nanoscale Near-Field Tomography of Surface States on (Bi _{0.5} Sb _{0.5}) ₂ Te ₃ . Nano Letters, 2018, 18, 7515-7523.	4.5	50
46	SiGeSn growth studies using reduced pressure chemical vapor deposition towards optoelectronic applications. Thin Solid Films, 2014, 557, 183-187.	0.8	48
47	Effect of growth parameters on the interfacial structure of GaInAs/InP quantum wells. Journal of Crystal Growth, 1991, 107, 537-542.	0.7	47
48	Flux periodic magnetoconductance oscillations in GaAs/InAs core/shell nanowires. Physical Review B, 2014, 89, .	1.1	47
49	Ballistic Transport and Exchange Interaction in InAs Nanowire Quantum Point Contacts. Nano Letters, 2016, 16, 3116-3123.	4.5	46
50	Electronic structure, surface morphology, and topologically protected surface states of Sb ₂ Te ₃ thin films grown on Si(111). Journal of Applied Physics, 2013, 113, .	1.1	45
51	Nanoimprint and selective-area MOVPE for growth of GaAs/InAs core/shell nanowires. Nanotechnology, 2013, 24, 085603.	1.3	45
52	Activation of Zn and Cd acceptors in InP grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 1989, 54, 2411-2413.	1.5	44
53	Supercurrent in Nb/InAs-nanowire/Nb Josephson junctions. Journal of Applied Physics, 2012, 112, .	1.1	43
54	Realization of nanoscaled tubular conductors by means of GaAs/InAs core/shell nanowires. Nanotechnology, 2013, 24, 035203.	1.3	43

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55	Quantum Transport and Nano Angle-resolved Photoemission Spectroscopy on the Topological Surface States of Single Sb ₂ Te ₃ Nanowires. Scientific Reports, 2016, 6, 29493.	1.6	43
56	Finite interface effects for thin GaInAs/InP quantum wells grown by LP-MOVPE with a growth interruption sequence. Journal of Crystal Growth, 1991, 107, 543-548.	0.7	42
57	In situ scanning tunneling microscopy study of C-induced Ge quantum dot formation on Si(100). Applied Physics Letters, 1999, 74, 994-996.	1.5	42
58	Misfit dislocation free InAs/GaSb core-shell nanowires grown by molecular beam epitaxy. Nanoscale, 2015, 7, 356-364.	2.8	42
59	Coexistence of weak localization and a metallic phase in Si/SiGe quantum wells. Physical Review B, 2000, 61, R5082-R5085.	1.1	41
60	Growth, characterization, and transport properties of ternary (Bi _{1-x} Sb _x) ₂ Te ₃ topological insulator layers. Journal of Physics Condensed Matter, 2016, 28, 495501.	0.7	41
61	Growth and analysis of quantum well structures. Journal of Crystal Growth, 1991, 107, 520-530.	0.7	40
62	Fabrication and characterization of freestanding Si/Cr micro- and nanospirals. Microelectronic Engineering, 2006, 83, 1237-1240.	1.1	40
63	Tuning the Dirac point to the Fermi level in the ternary topological insulator (Bi _{1-x} Sb _x) ₂ Te ₃ . Applied Physics Letters, 2015, 107, .	1.5	40
64	SiGeSn Ternaries for Efficient Group IV Heterostructure Light Emitters. Small, 2017, 13, 1603321.	5.2	40
65	Free-standing Si/SiGe micro- and nano-objects. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 23, 280-284.	1.3	38
66	Ge quantum dot molecules and crystals: Preparation and properties. Surface Science, 2007, 601, 2787-2791.	0.8	38
67	Direct electro-optical pumping for hybrid CdSe nanocrystal/III-nitride based nano-light-emitting diodes. Applied Physics Letters, 2016, 108, 061107.	1.5	38
68	Magnetoluminescence study of many-body effects in homogeneous quasi-two-dimensional electron-hole plasma in undoped In _x Ga _{1-x} As/InP single quantum wells. Physical Review B, 1991, 44, 10680-10688.	1.1	37
69	MOVPE of n-doped GaAs and modulation doped GaAs/AlGaAs nanowires. Journal of Crystal Growth, 2010, 312, 635-640.	0.7	37
70	Influence of growth temperature on the selective area MOVPE of InAs nanowires on GaAs (111) B using N ₂ carrier gas. Journal of Crystal Growth, 2009, 311, 3813-3816.	0.7	36
71	Electrical Spin Injection into InN Semiconductor Nanowires. Nano Letters, 2012, 12, 4437-4443.	4.5	36
72	P _n Junctions in Ultrathin Topological Insulator Sb ₂ Te ₃ /Bi ₂ Te ₃ Heterostructures Grown by Molecular Beam Epitaxy. Crystal Growth and Design, 2016, 16, 2057-2061.	1.4	36

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73	Spin polarization limit in Bi ₂ Te ₃ Dirac cone studied by angle- and spin-resolved photoemission experiments and <i>ab initio</i> calculations. <i>Physical Review B</i> , 2013, 87, .	1.1	35
74	Diffusion of Zn acceptors during MOVPE of InP. <i>Journal of Crystal Growth</i> , 1991, 108, 449-454.	0.7	33
75	Excitons in dense two-dimensional electron-hole magnetoplasmas. <i>Physical Review B</i> , 1992, 46, 12765-12768.	1.1	32
76	Analysis of the Metallic Phase of Two-Dimensional Holes in SiGe in Terms of Temperature Dependent Screening. <i>Physical Review Letters</i> , 2000, 85, 4357-4360.	2.9	32
77	Selective area growth of Bi ₂ Te ₃ and Sb ₂ Te ₃ topological insulator thin films. <i>Journal of Crystal Growth</i> , 2016, 443, 38-42.	0.7	32
78	Optical properties of very narrow GaInAs/InP quantum wells grown by low-pressure metalorganic vapor phase epitaxy. <i>Applied Physics Letters</i> , 1988, 52, 872-873.	1.5	31
79	Nanometer lithography for III-V semiconductor wires using chloromethylated poly- α -methylstyrene resist. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1988, 6, 2308.	1.6	31
80	Self-organized growth of Ge quantum dots on Si(001) substrates induced by sub-monolayer C coverages. <i>Nanotechnology</i> , 1999, 10, 122-126.	1.3	31
81	Axial strain in GaAs/InAs core-shell nanowires. <i>Applied Physics Letters</i> , 2013, 102, .	1.5	31
82	Manipulating InAs nanowires with submicrometer precision. <i>Review of Scientific Instruments</i> , 2011, 82, 113705.	0.6	30
83	Broadband transmission masks, gratings and filters for extreme ultraviolet and soft X-ray lithography. <i>Thin Solid Films</i> , 2012, 520, 5080-5085.	0.8	30
84	Controlled wurtzite inclusions in self-catalyzed zinc blende III-V semiconductor nanowires. <i>Journal of Crystal Growth</i> , 2013, 378, 506-510.	0.7	30
85	Nucleation of Ge quantum dots on the C-alloyed Si(001) surface. <i>Thin Solid Films</i> , 2000, 380, 176-179.	0.8	29
86	Resolving ambiguities in nanowire field-effect transistor characterization. <i>Nanoscale</i> , 2015, 7, 18188-18197.	2.8	29
87	Electrical resistance of individual defects at a topological insulator surface. <i>Nature Communications</i> , 2017, 8, 15704.	5.8	29
88	Infrared/terahertz spectra of the photogalvanic effect in (Bi,Sb)Te based three-dimensional topological insulators. <i>Physical Review Materials</i> , 2018, 2, .	0.9	29
89	Nucleation of Ge dots on the C-alloyed Si(001) surface. <i>Physical Review B</i> , 2002, 66, .	1.1	28
90	Hall mobility of narrow Si _{0.2} Ge _{0.8} -Si quantum wells on Si _{0.5} Ge _{0.5} relaxed buffer substrates. <i>Applied Physics Letters</i> , 2004, 84, 2829-2831.	1.5	28

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91	Impact of template variations on shape and arrangement of Si ^δ -Ge quantum dot arrays. Applied Physics Letters, 2008, 92, .	1.5	28
92	Photoluminescence study of interdiffusion in In _{0.53} Ga _{0.47} As/InP surface quantum wells. Applied Physics Letters, 1992, 60, 2660-2662.	1.5	27
93	Intersubband absorption performed on p-type modulation-doped Si _{0.2} Ge _{0.8} /Si quantum wells grown on Si _{0.5} Ge _{0.5} pseudosubstrate. Applied Physics Letters, 2002, 80, 3274-3276.	1.5	27
94	Crystal Phase Selective Growth in GaAs/InAs Core-Shell Nanowires. Crystal Growth and Design, 2014, 14, 1167-1174.	1.4	27
95	Formation and ordering effects of C-induced Ge dots grown on Si (001) by molecular beam epitaxy. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2000, 74, 222-228.	1.7	26
96	Nanorobotics for creating NEMS from 3D helical nanostructures. Journal of Physics: Conference Series, 2007, 61, 257-261.	0.3	26
97	Crystal Phase Transformation in Self-Assembled InAs Nanowire Junctions on Patterned Si Substrates. Nano Letters, 2016, 16, 1933-1941.	4.5	26
98	Two-dimensional arrays of self-organized Ge islands obtained by chemical vapor deposition on pre-patterned silicon substrates. Nanotechnology, 2007, 18, 455307.	1.3	25
99	Photoluminescence studies of SiGe quantum dot arrays prepared by templated self-assembly. Europhysics Letters, 2008, 84, 67017.	0.7	25
100	X-ray diffraction investigation of a three-dimensional Si/SiGe quantum dot crystal. Physical Review B, 2009, 79, .	1.1	25
101	Structural and optical properties of InGa _N -GaN nanowire heterostructures grown by molecular beam epitaxy. Journal of Applied Physics, 2011, 109, 014309.	1.1	25
102	Opto-electronic characterization of three dimensional topological insulators. Journal of Applied Physics, 2016, 120, .	1.1	25
103	Fabrication and optical characterization of quantum wires from semiconductor materials with varying In content. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1989, 7, 2030.	1.6	24
104	Ultra flexible SiGe/Si/Cr nanosprings. Microelectronics Journal, 2008, 39, 478-481.	1.1	24
105	Crossover from Josephson Effect to Single Interface Andreev Reflection in Asymmetric Superconductor/Nanowire Junctions. Nano Letters, 2014, 14, 4977-4981.	4.5	24
106	Adiabatic Edge Channel Transport in a Nanowire Quantum Point Contact Register. Nano Letters, 2016, 16, 4569-4575.	4.5	24
107	Magnetotransport studies of δ -doping layers in MOCVD-grown InP. Semiconductor Science and Technology, 1989, 4, 16-19.	1.0	23
108	High-performance undoped InP/n-In/sub 0.53/Ga/sub 0.47/As MSM photodetectors grown by LP-MOVPE. IEEE Transactions on Electron Devices, 1992, 39, 1028-1031.	1.6	23

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109	Three-dimensional phononic nanocrystal composed of ordered quantum dots. Applied Physics Letters, 2010, 96, .	1.5	23
110	Core-shell CdTe-TiO ₂ nanostructured solar cell. Journal of Materials Chemistry, 2012, 22, 10441.	6.7	23
111	Electronic Transport with Dielectric Confinement in Degenerate InN Nanowires. Nano Letters, 2012, 12, 2768-2772.	4.5	23
112	Nano-light-emitting-diodes based on InGaN mesoscopic structures for energy saving optoelectronics. Applied Physics Letters, 2016, 109, .	1.5	23
113	Magnetotransport in narrow In _{0.53} Ga _{0.47} As/InP wires. Applied Physics Letters, 1990, 57, 1757-1759.	1.5	22
114	Hot-hole effects in a dilute two-dimensional gas in SiGe. Europhysics Letters, 2003, 61, 499-505.	0.7	22
115	Novel nanostructure architectures. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 25, 280-287.	1.3	22
116	Domain formation due to surface steps in topological insulator Bi ₂ Te ₃ thin films grown on Si (111) by molecular beam epitaxy. Applied Physics Letters, 2013, 103, .	1.5	22
117	MBE growth of Al/InAs and Nb/InAs superconducting hybrid nanowire structures. Nanoscale, 2017, 9, 16735-16741.	2.8	22
118	Quantum Transport in Topological Surface States of Selectively Grown Bi ₂ Te ₃ Nanoribbons. Advanced Electronic Materials, 2020, 6, 2000205.	2.6	21
119	Enhanced light scattering of the forbidden longitudinal optical phonon mode studied by micro-Raman spectroscopy on single InN nanowires. Nanotechnology, 2010, 21, 315702.	1.3	20
120	Si substrate preparation for the VS and VLS growth of InAs nanowires. Physica Status Solidi - Rapid Research Letters, 2013, 7, 840-844.	1.2	20
121	Topography and structure of ultrathin topological insulator Sb ₂ Te ₃ films on Si(111) grown by means of molecular beam epitaxy. Journal of Crystal Growth, 2016, 453, 158-162.	0.7	20
122	Selective growth of Si/SiGe resonant tunneling diodes by atmospheric pressure chemical vapor deposition. Applied Physics Letters, 1992, 61, 2872-2874.	1.5	19
123	Observation of valence-band Landau-level mixing by resonant magnetotunneling. Physical Review B, 1993, 47, 16036-16039.	1.1	19
124	Cost estimate of electricity produced by TPV. Semiconductor Science and Technology, 2003, 18, S254-S261.	1.0	19
125	Evolution and stability of ordered SiGe islands grown on patterned Si(100) substrates. Journal of Applied Physics, 2009, 105, .	1.1	19
126	InAlN/GaN/Si heterostructures and field-effect transistors with lattice matched and tensely or compressively strained InAlN. Applied Physics Letters, 2010, 97, 173505.	1.5	19

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127	Enhanced Raman Scattering of Ultramarine on Au-coated Ge/Si-nanostructures. <i>Plasmonics</i> , 2011, 6, 413-418.	1.8	19
128	Controlled uniform growth of GaInAsP/InP structures for laser application on 2 inch wafers by LP-MOVPE at 20 mbar. <i>Journal of Crystal Growth</i> , 1988, 93, 285-291.	0.7	18
129	Resonance spectroscopy of InGaAs/InP quantum well sub-bands. <i>Semiconductor Science and Technology</i> , 1988, 3, 797-801.	1.0	18
130	Photoconductivity in InGaAs/InP quantum well heterostructures-inter-sub-band and sub-band-continuum transitions. <i>Semiconductor Science and Technology</i> , 1988, 3, 1029-1036.	1.0	17
131	Size control of carbon-induced Ge quantum dots. <i>Applied Physics Letters</i> , 2000, 77, 3218-3220.	1.5	17
132	Directed batch assembly of three-dimensional helical nanobelts through angular winding and electroplating. <i>Nanotechnology</i> , 2007, 18, 055304.	1.3	17
133	In situ investigations of Si and Ge interdiffusion in Ge-rich Si/SiGe multilayers using x-ray scattering. <i>Semiconductor Science and Technology</i> , 2007, 22, 447-453.	1.0	17
134	Tensile strained SiGe quantum well infrared photodetectors based on a light-hole ground state. <i>Applied Physics Letters</i> , 2011, 98, .	1.5	17
135	Site-controlled growth of indium nitride based nanostructures using metalorganic vapour phase epitaxy. <i>Journal of Crystal Growth</i> , 2013, 370, 336-341.	0.7	17
136	Giant Magnetoconductance Oscillations in Hybrid Superconductor~Semiconductor Core/Shell Nanowire Devices. <i>Nano Letters</i> , 2014, 14, 6269-6274.	4.5	17
137	Optical and structural properties of MOVPE grown GaIn _{1-x} As/InP strained multiple quantum well astructures. <i>Journal of Electronic Materials</i> , 1992, 21, 293-298.	1.0	16
138	Sensitivity Enhancement of Metal~Semiconductor ~Metal Photodetectors on Low-Temperature-Grown GaAs Using Alloyed Contacts. <i>IEEE Photonics Technology Letters</i> , 2008, 20, 1054-1056.	1.3	16
139	SiGe quantum well infrared photodetectors on pseudosubstrate. <i>Applied Physics Letters</i> , 2009, 94, .	1.5	16
140	Femtosecond and highly sensitive GaAs metal~semiconductor~metal photodetectors grown on aluminum mirrors/pseudo-substrates. <i>Semiconductor Science and Technology</i> , 2010, 25, 075001.	1.0	16
141	Preparation of Ohmic contacts to GaAs/AlGaAs-core/shell-nanowires. <i>Applied Physics Letters</i> , 2012, 100, .	1.5	16
142	Coherent ultrafast spin-dynamics probed in three dimensional topological insulators. <i>Scientific Reports</i> , 2015, 5, 15304.	1.6	16
143	LP-MOCVD growth and characterization of undoped and modulation doped GaInAsP/InP and GaInAs/InP multi quantum wells. <i>Journal of Crystal Growth</i> , 1988, 93, 382-388.	0.7	15
144	Boron redistribution in arsenic~implanted silicon and short~channel effects in metal~oxide~semiconductor field effect transistors. <i>Applied Physics Letters</i> , 1992, 61, 3038-3040.	1.5	15

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145	In-plane valence-band nonparabolicity and anisotropy in strained Si-Ge quantum wells. <i>Physical Review B</i> , 1993, 48, 15112-15115.	1.1	15
146	Anomalous magnetoresistance peak in quantum wires: Evidence for boundary-scattering mechanisms. <i>Physical Review B</i> , 1993, 47, 6524-6528.	1.1	15
147	Band gap and band alignment of strain reduced Si/Si _{1-x} Ge _x multiple quantum well structures obtained by photoluminescence measurements. <i>Applied Physics Letters</i> , 1998, 73, 1257-1259.	1.5	15
148	Single-hole transistor in a p-Si/SiGe quantum well. <i>Applied Physics Letters</i> , 2001, 78, 341-343.	1.5	15
149	Strain compensated Si/Si _{0.2} Ge _{0.8} quantum cascade structures grown by low temperature molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2003, 251, 707-717.	0.7	15
150	Intersubband absorption of strain-compensated Si _{1-x} Ge _x valence-band quantum wells with 0.7 eV. <i>Journal of Applied Physics</i> , 2005, 98, 044501.	1.1	15
151	Templated self-organization of SiGe quantum structures for nanoelectronics. <i>Materials Science and Engineering C</i> , 2007, 27, 947-953.	3.8	15
152	Subpicosecond electron-hole recombination time and terahertz-bandwidth photoresponse in freestanding GaAs epitaxial mesoscopic structures. <i>Applied Physics Letters</i> , 2012, 101, .	1.5	15
153	Phase coherent transport in InSb nanowires. <i>Applied Physics Letters</i> , 2012, 101, 082103.	1.5	15
154	Generation of circularly polarized radiation from a compact plasma-based extreme ultraviolet light source for tabletop X-ray magnetic circular dichroism studies. <i>Review of Scientific Instruments</i> , 2014, 85, 103110.	0.6	15
155	In _{0.53} Ga _{0.47} As/InP quantum wires: Fabrication and magnetotransport studies. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1990, 8, 1353.	1.6	14
156	Monolithic Integration of Ultrafast Photodetector and MESFET in the GaN Material System. <i>IEEE Photonics Technology Letters</i> , 2011, 23, 1189-1191.	1.3	14
157	Non-uniform distribution of induced strain in a gate-recessed AlGaIn/GaN structure evaluated by micro-PL measurements. <i>Semiconductor Science and Technology</i> , 2012, 27, 105008.	1.0	14
158	In situ disentangling surface state transport channels of a topological insulator thin film by gating. <i>Npj Quantum Materials</i> , 2018, 3, .	1.8	14
159	Reappearance of first Shapiro step in narrow topological Josephson junctions. <i>Science Advances</i> , 2021, 7, .	4.7	14
160	MIMIC-compatible GaAs and InP field effect controlled transferred electron (FECTED) oscillators. <i>IEEE Transactions on Microwave Theory and Techniques</i> , 1989, 37, 2093-2098.	2.9	13
161	Absorption measurement of strained SiGe nanostructures deposited by UHV-CVD. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2003, 16, 481-488.	1.3	13
162	Shape and composition change of Ge dots due to Si capping. <i>Applied Surface Science</i> , 2004, 224, 139-142.	3.1	13

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163	Magnetoresistance oscillations in MBE-grown Sb ₂ Te ₃ thin films. Applied Physics Letters, 2017, 110, .	1.5	13
164	Stencil lithography of superconducting contacts on MBE-grown topological insulator thin films. Journal of Crystal Growth, 2017, 477, 183-187.	0.7	13
165	Properties of the two-dimensional electron gas in modulation-doped GaInAs(P)/InP structures grown by low-pressure metalorganic vapor-phase epitaxy. Journal of Applied Physics, 1989, 66, 697-703.	1.1	12
166	Electron-hole transition energies and atomic steps at the interfaces of thin InGaAs/InP quantum wells. Applied Physics Letters, 1990, 56, 632-634.	1.5	12
167	Fabrication of SiGe/Si/Cr bent cantilevers based on self-rolling of epitaxial films. Microelectronic Engineering, 2003, 67-68, 595-601.	1.1	12
168	Direct monitoring of the excited state population in biased SiGe valence band quantum wells by femtosecond resolved photocurrent experiments. Applied Physics Letters, 2006, 89, 211111.	1.5	12
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